## ELECTRONIC AND STRUCTURAL PROPERTIES OF FERECRYSTALLINE COMPOUNDS INVESTIGATED BY PHOTOELECTRON SPECTROSCOPY

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Fig. 1. **Top:** XPS Pb5d spectra of a (PbSe)<sub>1</sub>(NbSe<sub>2</sub>)<sub>2</sub> ferecrystal and binary PbSe. **Bottom:** Schematic representation of the structure of a (MSe)<sub>1</sub>(NbSe<sub>2</sub>)<sub>2</sub> ferecrystal. The groundbreaking work on graphene by Novoselov and Geim [1] sparked a run on 2D materials. A combination of different sheet-like materials offers new possibilities in materials properties. The method of *modulated elemental reactants (MER)* [2] enables the preparation of designed turbostratically disordered intergrowths of 2D materials, termed *ferecrystals* [3].

In this work, we investigated the electronic structure of several  $(MSe)_1(NbSe_2)_2$  ferecrystals using X-ray photoelectron spectroscopy (XPS). Core level and valence band spectra of ferecrystals with M = Pb or Sn were compared to their respective MER-produced binary compounds MSe and NbSe<sub>2</sub>. We found evidence of inter-layer interactions and charge transfer as Pb and Sn core levels shift towards lower binding energies in the ferecrystal (Fig. 1).

With XPS, we could also confirm a decrease in the number of antiphase boundaries in  $(BiSe)_1$  $(NbSe_2)_n$ , when the spacing between the BiSe layers is increased from n = 1 to 2 layers of NbSe<sub>2</sub>. Antiphase boundaries are a structural modulation oc-

curring in compounds with M = Bi, where Bi-Se bonds are periodically substituted by Bi-Bi bonds [4] (Fig. 2).

Keywords: Ferecrystals; Layered Compounds; XPS; Charge Transfer

## References

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